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# N-Channel 200 V (D-S) 175 °C MOSFET

#### **DESCRIPTION**

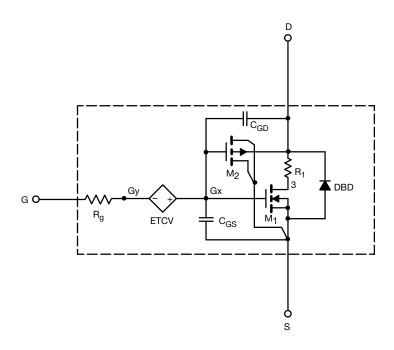
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### **CHARACTERISTICS**

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over -55 °C to +125 °C temperature range
- · Model the gate charge

#### SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.





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SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	3.5	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	0.0126	0.0123	Ω
		$V_{GS} = 7.5 \text{ V}, I_D = 30 \text{ A}$	0.0133	0.0130	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	98	63	S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 30 A	0.84	0.85	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	3030	3120	pF
Output Capacitance	Coss		305	280	
Reverse Transfer Capacitance	C <sub>rss</sub>		60	24	
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A	54	58	nC
Gate-Source Charge	Q <sub>gs</sub>		17.6	17.6	
Gate-Drain Charge	$Q_{gd}$		17.2	17.2	

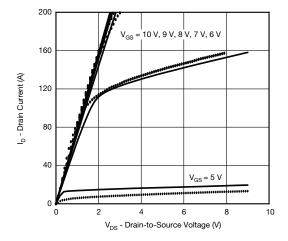
#### Notes

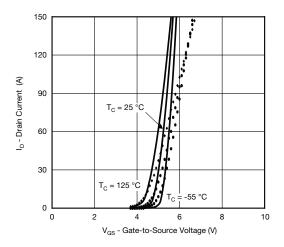
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

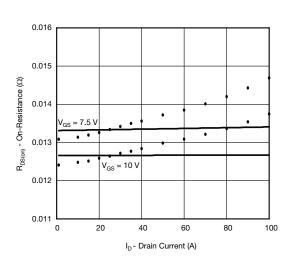
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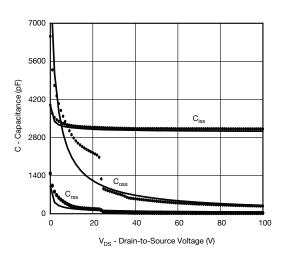
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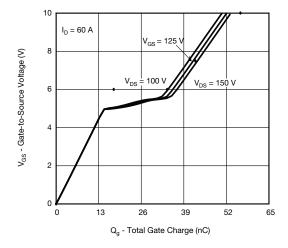
### **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25$ °C, unless otherwise noted)

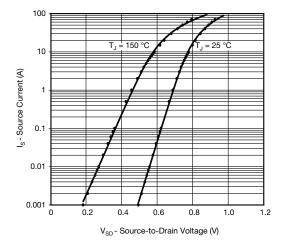












#### Note

· Dots and squares represent measured data.

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